

**Features**

- APD with 0.04 mm<sup>2</sup> active area
- Slow multiplication curve
- QE > 80% @ 750 nm-910 nm
- Fast rise time, low noise
- Optimum gain: 50-60

**Description**

Circular active area APD chip with NIR enhanced sensitivity. Metal can type hermetic TO52 package with clear glass window.

**Application**

- Laser range finder
- High speed photometry
- High speed optical communications
- Medical equipment

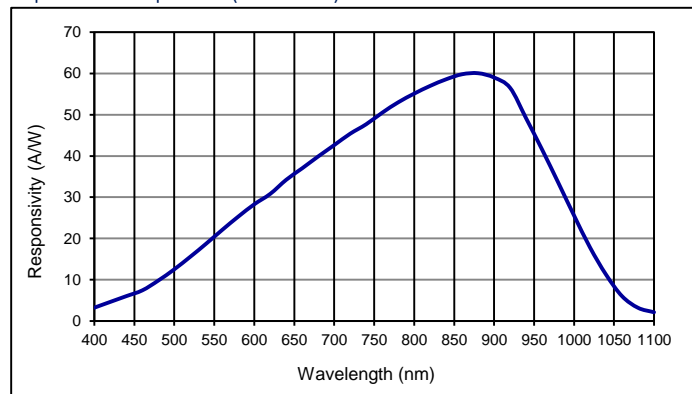
**RoHS**

2011/65/EU

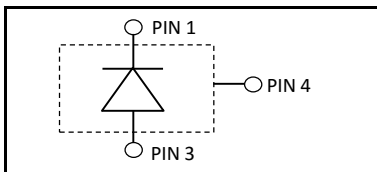
**Absolute maximum ratings**

| Symbol            | Parameter                     | Min | Max  | Unit |
|-------------------|-------------------------------|-----|------|------|
| T <sub>STG</sub>  | Storage temp                  | -55 | 125  | °C   |
| T <sub>OP</sub>   | Operating temp                | -40 | 100  | °C   |
| M <sub>max</sub>  | Gain (I <sub>PO</sub> = 1 nA) | 200 |      |      |
| I <sub>PEAK</sub> | Peak DC current               |     | 0.25 | mA   |

**Spectral response (M = 100)**



**Schematic**

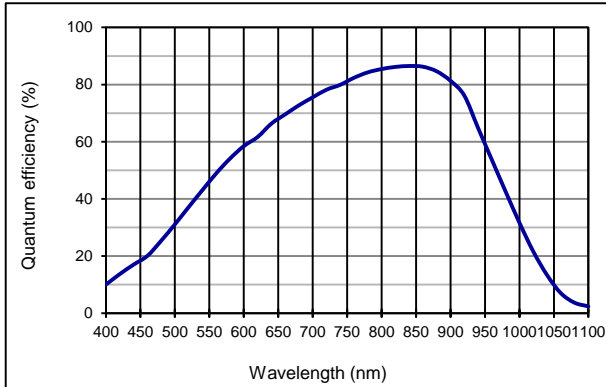


**Electro-optical characteristics @ 23 °C**

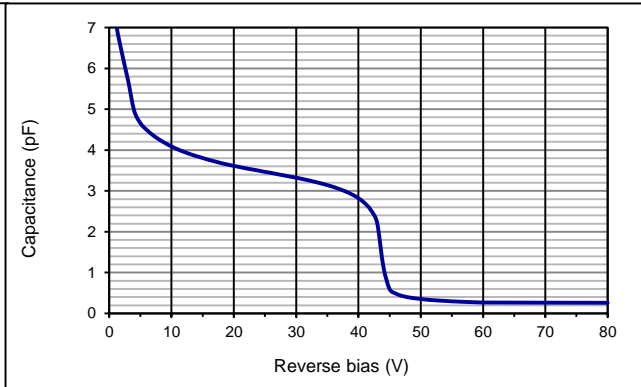
| Symbol          | Characteristic          | Test Condition                             | Min          | Typ | Max  | Unit            |
|-----------------|-------------------------|--|--------------|-----|------|-----------------|
|                 | Active area             |  | diameter 230 |     |      | µm              |
|                 | Active area             |  | 0.04         |     |      | mm <sup>2</sup> |
| I <sub>D</sub>  | Dark current            | M = 100                                    |              | 0.5 | 1    | nA              |
| C               | Capacitance             | M = 100                                    |              | 0.3 |      | pF              |
|                 | Responsivity            | M = 100; λ = 905 nm                        | 52           | 58  | 60   | A/W             |
| t <sub>R</sub>  | Rise time               | M = 100; λ = 905 nm; R <sub>L</sub> = 50 Ω |              | 0.5 |      | ns              |
|                 | Cut-off frequency       | -3dB                                       |              | 0.6 |      | GHz             |
| V <sub>BR</sub> | Breakdown voltage       | I <sub>R</sub> = 2 µA                      | 160          |     | 200  | V               |
|                 | Temperature coefficient | Change of V <sub>BR</sub> with temperature | 1.25         |     | 1.55 | V/K             |
|                 | Excess noise factor     | M = 100                                    |              | 2.5 |      |                 |
|                 | Excess noise index      | M = 100                                    |              | 0.2 |      |                 |



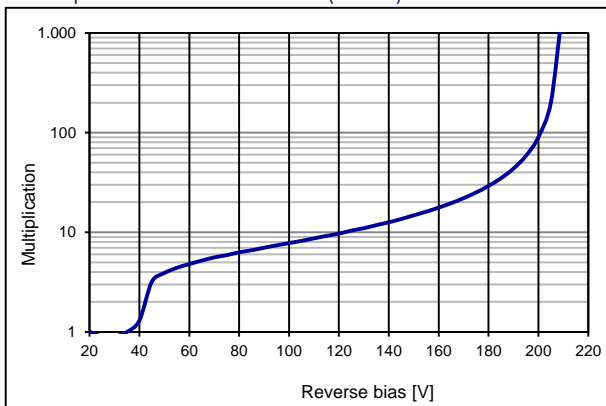
Quantum efficiency (23 °C)



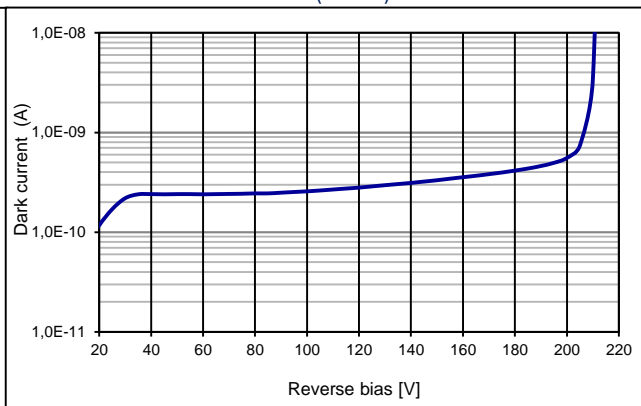
Capacitance as fct of reverse bias (23 °C)



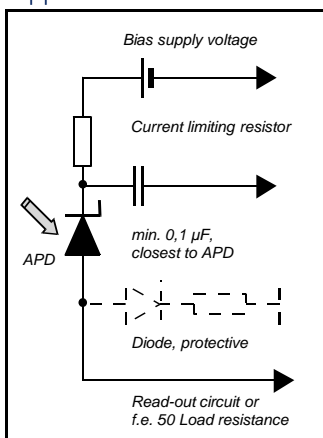
Multiplication as fct of bias (23 °C)



Dark current as fct of bias (23 °C)



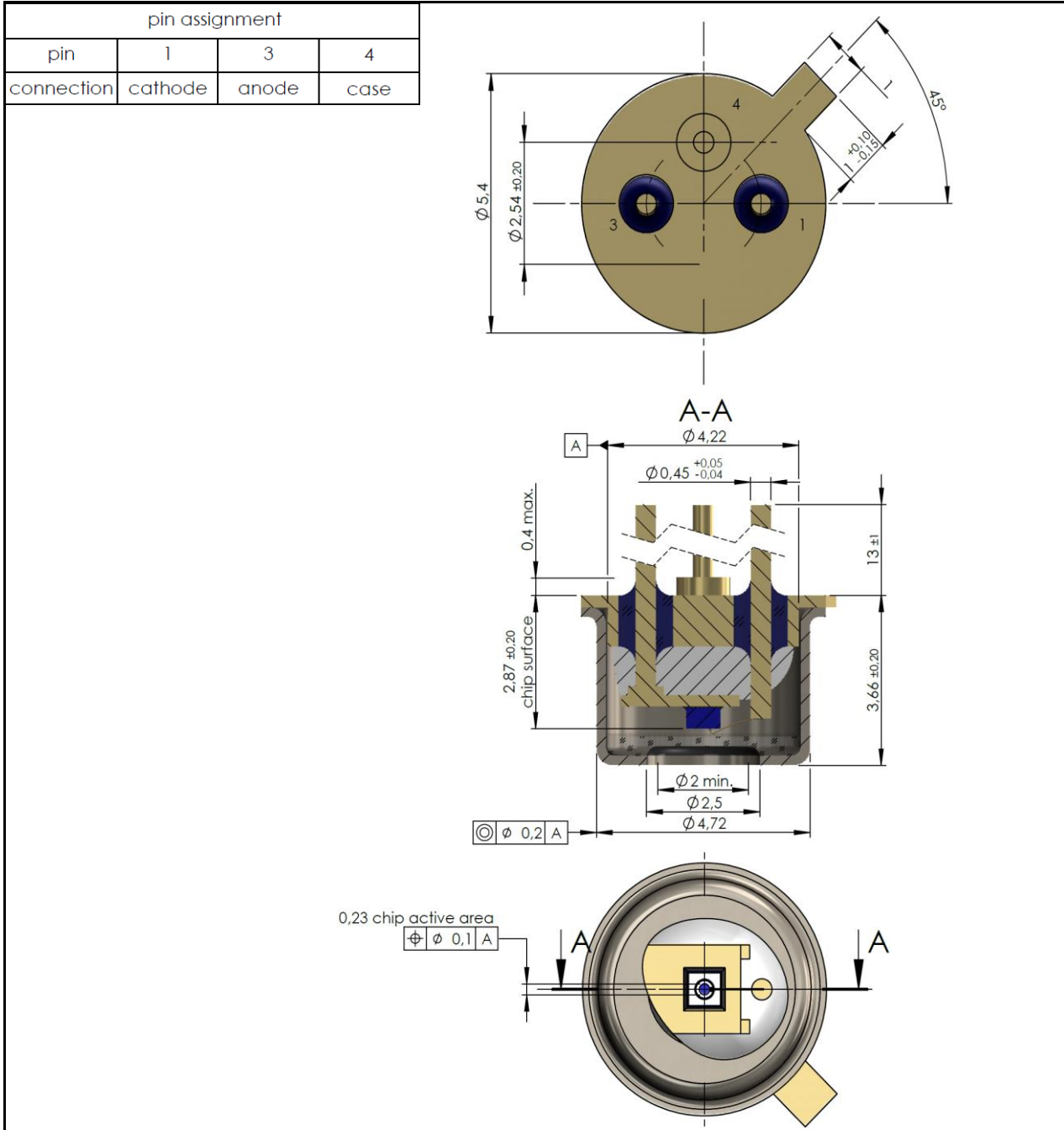
Application hints:



- Current should be limited by a protecting resistor or current limiting - IC inside the power supply
- For low light level applications blocking of ambient light should be used
- For high gain applications bias voltage should be temperature compensated
- Please consider basic ESD protection while handling
- Use low noise read-out - IC
- For further questions please refer to document "Instructions for handling and processing"
- Optimum gain: 50-60



Technical Drawing, Package: T052



Package dimension:

Small quantities: Foam pad, boxed (12 cm x 16.5 cm)

Disclaimer: Due to our strive for continuous improvement, specifications are subject to change within our PCN policy according to JESD46C.